

L Number	Hits	Search Text	DB	Time stamp
1	467577	integrated near circuit	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/18 07:13
2	355	((porous same (silica silicate silicalite)) and (((binder) same (radiation photosensitive ultraviolet)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/18 07:45
3	4	((integrated near circuit) and ((porous same (silica silicate silicalite)) and (((binder) same (radiation photosensitive ultraviolet))))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/18 07:14
4	76	((porous near (silica silicate silicalite (silicon near dioxide) sio?sub.2)) and (((binder) same (radiation photosensitive ultraviolet)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/18 07:46
5	2	((integrated near circuit) and ((porous near (silica silicate silicalite (silicon near dioxide) sio?sub.2)) and (((binder) same (radiation photosensitive ultraviolet))))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/18 07:46
6	0	((integrated near circuit) and ((porous near (silica silicate silicalite (silicon near dioxide) sio?sub.2)) and (((binder) same (radiation photosensitive ultraviolet))))) not ((integrated near circuit) and ((porous same (silica silicate silicalite)) and (((binder) same (radiation photosensitive ultraviolet)))))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/18 07:51
7	34917	((integrated near circuit) and (metal near layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/18 07:51
8	17576	((integrated near circuit) and (metal near layer)) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/18 08:00
9	8079	((integrated near circuit) and (metal near layer)) and wafer and (dielectric near layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/18 08:00
10	1045	((integrated near circuit) and (metal near layer)) and wafer and (dielectric near layer)) and silica	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/18 08:00
11	6563	((integrated near circuit) and (metal near layer)) and (silicon near wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/18 08:00
12	3025	((integrated near circuit) and (metal near layer)) and (silicon near wafer)) and (dielectric near layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/18 08:00
13	7	((integrated near circuit) and (metal near layer)) and (silicon near wafer)) and (dielectric near layer)) and 252/570;524/588;522/99,148;528/32.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/18 08:01